

**Amendments to the Specification:**

Please replace paragraph [0004] with the following amended paragraph:

**[0004]** A monolayer of partially decomposed source gas molecules (e.g.,  $\text{SiH}_4$  or  $\text{SiH}_2\text{Cl}_2$ ) is adsorbed over the substrate or surface. The adsorbate may consists of a silicon atom and at least another kind of atom or group bonded with silicon, such as chlorine, hydrogen or methyl (e.g.,  $\text{SiCl}_n$ ,  $\text{SiH}_n$  or  $\text{H}_{4-n}\text{SiMe}_n$ , where  $n=1-4$ ). The adsorbate decomposes to form adatoms of silicon on the surface. The adatoms migrate or diffuse on the surface to an empty lattice site of the silicon crystal. The crystal continues to form and grow as adatoms are generated on the crystalline surface and incorporated into the lattice. By-product removal is achieved and a new surface is created on the monolayer. The monolayer growth in the next cycle is made possible.

Please replace paragraph [0059] with the following amended paragraph:

**[0059]** Example 4: Amorphous silicon by CVD: A silicon dioxide layered wafer was loaded into the deposition chamber (Epi Centura<sup>®</sup> chamber) and subjected to a hydrogen purge for 1 minute [[s]]. A flow of carrier gas, hydrogen, was directed towards the substrate and the source compounds were added to the carrier flow. The silicon compound, 200 sccm of  $\text{HCl}_2\text{SiSiH}_3$ , was added to the chamber at 200 Torr and 40°C. The substrate was maintained at 40°C. Deposition was carried out for 3 minutes to form a 200 Å layer

Please replace paragraph [0076] with the following amended paragraph:

**[0076]** Example 21: Amorphous silicon by CVD: A silicon dioxide layered wafer was loaded into the deposition chamber (Epi Centura<sup>®</sup> chamber) and subjected to a hydrogen purge for 1 minute [[s]]. A flow of carrier gas, hydrogen, was directed towards the substrate and the source compounds were added to the carrier flow. The silicon compound, 200 sccm of  $\text{HCl}_2\text{SiSiH}_2\text{SiH}_3$ , was added to the chamber at 200 Torr and

40°C. The substrate was maintained at 40°C. Deposition was carried out for 3 minutes to form a 200 Å layer.

Please replace paragraph [0093] with the following amended paragraph:

**[0093]** Example 38: Amorphous silicon by CVD: A silicon dioxide layered wafer was loaded into the deposition chamber (Epi Centura<sup>®</sup> chamber) and subjected to a hydrogen purge for 1 minute [[s]]. A flow of carrier gas, hydrogen, was directed towards the substrate and the source compounds were added to the carrier flow. The silicon compound, 200 sccm of  $\text{HCl}_2\text{SiSiH}_2\text{SiH}_2\text{SiH}_2\text{SiH}_3$ , was added to the chamber at 200 Torr and 40°C. The substrate was maintained at 40°C. Deposition was carried out for 3 minutes to form a 200 Å layer.